TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π–MOSV)

2SK2545

DC-DC Converter, Relay Drive and Motor Drive Applications

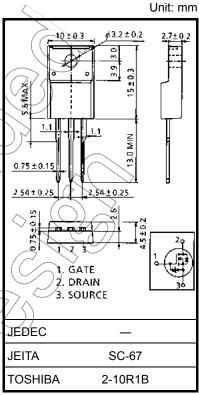
• Low drain–source ON resistance : $R_{DS\ (ON)} = 0.9\ \Omega(typ.)$ • High forward transfer admittance : $|Y_{fs}| = 5.5\ S\ (typ.)$

Low leakage current : I_{DSS} = 100 μA (max) (V_{DS} = 600 V)

• Enhancement mode : $V_{th} = 2.0 \text{ to } 4.0 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

				$/ \sim 1$
Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Drain-gate voltage (Ro	_{SS} = 20 kΩ)	V_{DGR}	600	V
Gate-source voltage		V_{GSS}	±30	V
Drain current	DC (Note 1)	ΙD	6	Α
	Pulse (Note 1)	I _{DP}	24	A
Drain power dissipation	r (Tc = 25°C)	PD	40	<\\w
Single pulse avalanche	energy (Note 2)	EAS	345	mJ
Avalanche current		TAR	6 <	\ A
Repetitive avalanche energy (Note 3)		EAR	4	/mJ
Channel temperature	((T _{ch}	150) °C
Storage temperature ra	inge	T _{stg}	-55 to 150	→°C



Weight: 1.9 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics Symbol	Max	Unit
Thermal resistance, channel to case Rth (ch-c)	3.125	°C/W
Thermal resistance, channel to ambient Rth (ch-a)	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD} = 90 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 16.8 mH, $R_G = 25 \Omega$, $I_{AR} = 6 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.

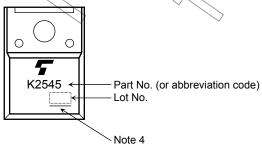
Electrical Characteristics (Ta = 25°C)

Charac	eteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	rrent	I_{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bre	eakdown voltage	V (BR) GSS	$I_{G} = \pm 10 \ \mu A, \ V_{GS} = 0 \ V$	±30	_	_	V
Drain cut-off cur	rent	I _{DSS}	V _{DS} = 600 V, V _{DS} = 0 V		_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold v	roltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0) /~	4.0	V
Drain-source OI	N resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 3 A	\nearrow	0.9	1.25	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 3 A	2.0	5.5	_	S
Input capacitano	e	C _{iss}		_	1300	_	
Reverse transfer	capacitance	C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	130	_	pF
Output capacitar	nce	C _{oss}		_	400		
T Switching time F	Rise time	t _r	V _{GS} _{0V}	- (25	\\ \rangle \ \rangle	
	Turn-on time	t _{on}			45) –	
	Fall time	t _f		7(5)	40	_	ns
	Turn-off time	t _{off}	$V_{DD} = 300V$ Duty $\leq 1\%$, $t_{W} = 10\mu s$) -	150	_	
Total gate charg plus gate-drain)		Qg		_	30	_	
Gate-source cha	arge	Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 6 \text{ A}$	_	18		nC
Gate-drain ("mil	ler") charge	Q _{gd}		_	12	_	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Continuous drain reverse current (Note 1)	1 _{DR}		_	_	6	Α	
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	24	Α	
Forward voltage (diode)	V _{DSF}	I _{DR} = 6 A, V _{GS} = 0 V	_	_	-1.7	V	
Reverse recovery time	t _{rr}	I _{DR} = 6 A, V _{GS} = 0 V, dI _{DR} / dt = 100 A / μs	1	1000	-	ns	
Reverse recovery charge	Q _{rr}	1DR - 0 A, VGS - 0 V, diDR / dt - 100 A / μs		7.0	_	μC	





Note 4: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.